Dual N-Channel, Digital FET

FDG6301N-F085

Features

- 25 V, 0.22 A Continuous, 0.65 A Peak
- $R_{DS(ON)} = 4 \Omega @ V_{GS} = 4.5 V,$
- $R_{DS(ON)} = 5 \Omega @ V_{GS} = 2.7 V.$
- Very Low Level Gate Drive Requirements allowing Directop– Eration in 3 V Circuits (V_{GS(th)}<1.5 V)
- Gate–Source Zener for ESD Ruggedness (>6 kV Human Body Model)
- Compact Industry Standard SC70–6 Surface Mount Package.
- AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

• Low Voltage Applications as a Replacement for Bipolar Digital Transistors and Small Signal MOSFETs

Symbol	Parameter	Ratings	Units
VDSS	Drain to Source Voltage	25	V
Vgs	Gate to Source Voltage	8	V
lo	Drain Current Continuous	0.22	А
	Pulsed	0.65	
PD	Power Dissipation	0.3	W
Tj, Tsтg	Operating and Storage Temperature	-55 to 150	°C
ESD	Electrostatic Discharge Rating MIL–STD–883D Human Body Model (100 pF / 1500 W)	6.0	kV
R_{\thetaJA}	Thermal Resistance, Junction to Ambient	415	°C/W

MOSFET MAXIMUM RATINGS ($T_A = 25^{\circ}C$ unless otherwise noted)

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

- 1. R_{0JA} is the sum of the junction-to-case and case-to-ambient thermal resistance, where the case thermal reference is defined as the Solder mounting surface of the drain pins. R_{0JC} is guaranteed by design, while R_{0JA} is determined by the board design. R_{0JA} = 415 °C/W on minimum pad mounting on FR-4 board in still air.
- A suffix as "...F085P" has been temporarily introduced in order to manage a double source strategy as ON Semiconductor has officially announced in August 2014.
- 3. Pulse Test: Pulse Width < 300 μ s, Duty Cycle < 2.0%

ORDERING INFORMATION

Device	Device Marking	Package	Shipping [†]
FDG6301N-F085	FDG6301N	SC–88 (SC–70 6 Lead) (Pb–Free, Halogen Free)	3,000 units / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D

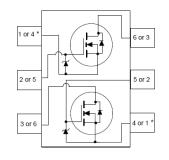


ON Semiconductor®

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SC-88 (SC-70 6 Lead), 1.25x2 CASE 419AD



FDG6301N-F085

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Parameter	Symbol	Test Conditions	Min	Тур	Max	Units
Off Characteristics			· · · ·			
Drain to Source Breakdown Voltage	Bvdss	$I_D = 250 \ \mu A, \ V_{GS} = 0 \ V$	25			V
Zero Gate Voltage Drain Current	IDSS	V _{DS} = 20 V, V _{GS} = 0 V			1	μA
		$T_{J} = $	55°C		10	
Gate to Source Leakage Current	lgss	$V_{GS} = \pm 8 V$			±100	nA
On Characteristics						
Gate to Source Threshold Voltage	VGS(th)	$V_{GS} = V_{DS}$, $I_D = 250 \ \mu A$	0.65	0.85	1.5	V
Drain to Source On Resistance	f DS(on)	I _D = 0.22 A, V _{GS} = 4.5 V		2.6	4	Ω
		I _D = 0.19 A, V _{GS} = 2.7 V		3.7	5	
		I _D = 0.22 A, V _{GS} = 4.5 V, T _J = 128	5°C	5.3	7	
On-State Drain Current	ID(on)	V _{GS} = 4.5 V, V _{DS} = 5 V	0.22			
Forward Transconductance	gfs	I _D = 0.22 A, V _{DS} = 5 V		0.2		s
Dynamic Characteristics						
Input Capacitance	Ciss	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz		9.5		pF
Output Capacitance	Coss			6		pF
Reverse Transfer Capacitance	Crss			4.5		pF
Total Gate Charge at –4.5 V	Qg(TOT)	V_{GS} = 0 to 4.5 V; V_{DD} = 5 V, I_D =	0.22 A	0.29	0.4	nC
Gate to Source Gate Charge	Qgs	$V_{DD} = 5 V, I_D = 0.22 A$		0.12		
Gate to Drain "Miller" Charge	Qgd			0.03		
Switching Characteristics						
Turn–On Delay Time	td(on)	$V_{DD} = 5 \text{ V}, \text{ I}_{D} = 0.5 \text{ A}, \text{ V}_{GS} = 4.5 \text{ V}}_{\text{GEN}} = 50 \Omega$	V,	5	10	ns
Rise Time	t _r			4.5	10	ns
Turn–Off Delay Time	td(off)			4	8	ns
Fall Time	t _f			3.2	7	ns
Drain–Source Diode Characteristics		-		ļ	ļ	
Maximum Continuous Source Current	ls				0.25	А
Source to Drain Diode Voltage	Vsd	I _{SD} = 0.25 A, V _{GS} = 0 V		0.8	1.2	V

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

FDG6301N-F085

TYPICAL CHARACTERISTICS

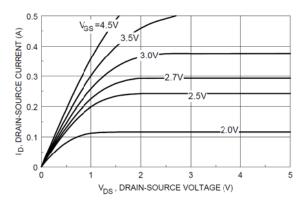


Figure 1. On–Region Characteristics

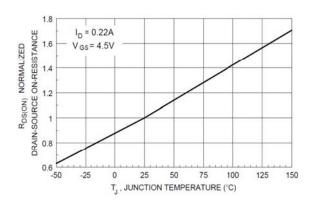


Figure 3. On–Resistance Variation with Temperature

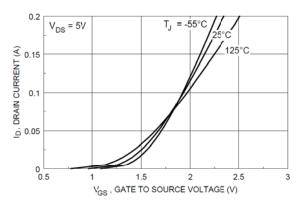


Figure 5. Transfer Characteristics

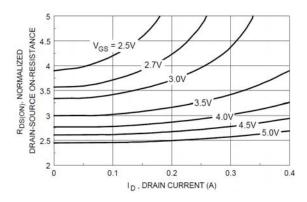


Figure 2. On–Resistance Variation with Drain Current and Gate Voltage

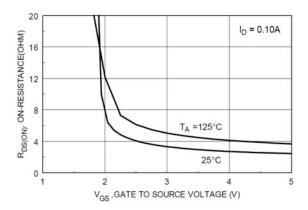


Figure 4. On–Resistance Variation with Gate–to–Source Voltage

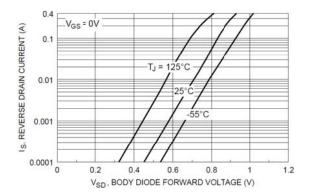


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

FDG6301N-F085

TYPICAL CHARACTERISTICS

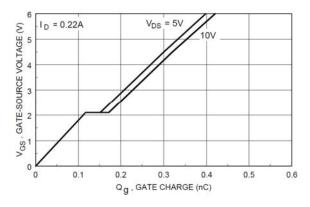


Figure 7. Gate Charge Characteristics

Ioms

25 40

100ms

100

10

1

0.3

0.1

0.03

0.01 L 0.4

DRAIN CURRENT (A)

NULIMIT

V_{GS} = 4.5V SINGLE PULSE

0.8

R₀JA = 415 °C/W T_A = 25°C

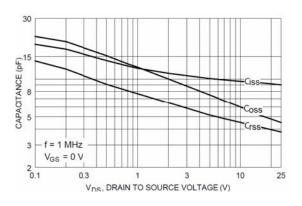


Figure 8. Capacitance Characteristics

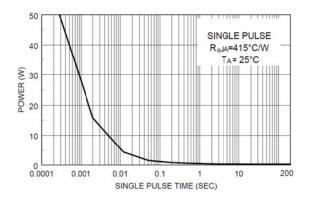


Figure 9. Maximum Safe Operating Area

5

V_{DS}, DRAIN-SOURCE VOLTAGE (V)

2

Figure 10. Single Pulse Maximum Power Dissipation

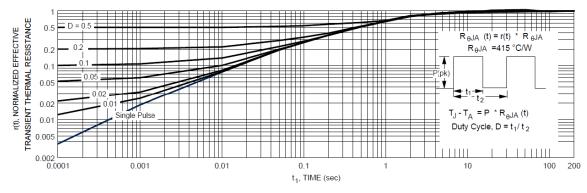
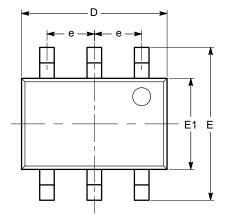


Figure 11. Transient Thermal Response Curve

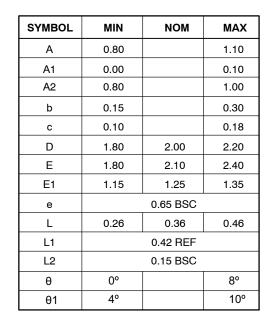
SC-88 (SC-70 6 Lead), 1.25x2 CASE 419AD ISSUE A

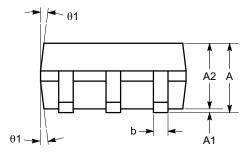
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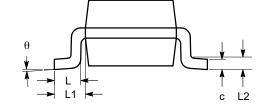


SIDE VIEW

Notes:

(1) All dimensions are in millimeters. Angles in degrees.

(2) Complies with JEDEC MO-203.



END VIEW

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